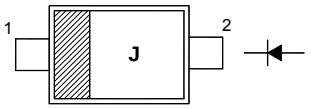
1SS06AWT

Schottky Barrier Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "**J**"
Simplified outline SOD-523 and symbol

Features

- Very low forward voltage
- Very low reverse current
- Ultra small SMD package

Applications

- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Low power consumption applications

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	40	V
Continuous Forward Current	I_F	200	mA
Repetitive Peak Forward Current $t_p \leq 1$ s	I_{FRM}	300	mA
Non-repetitive Peak Forward Current (t = 8.3 ms half sinewave)	I_{FSM}	1	A
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	- 65 to + 150	°C
Operating Ambient Temperature	T_{amb}	- 65 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 0.1 mA at I_F = 1 mA at I_F = 10 mA at I_F = 100 mA at I_F = 200 mA	V_F	 220 290 360 500 600	mV
Reverse Current at V_R = 25 V	I_R	0.5	µA
Diode Capacitance at V_R = 1 V, f = 1 MHz	C_D	20	pF

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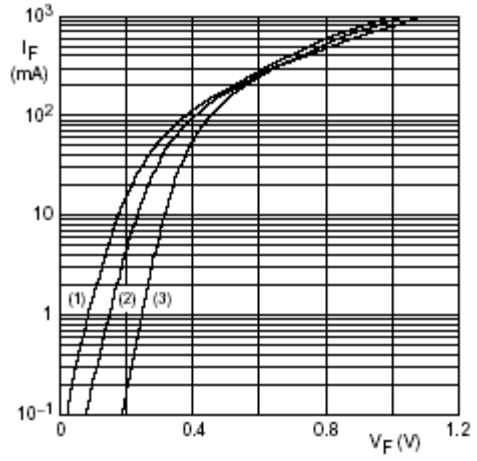
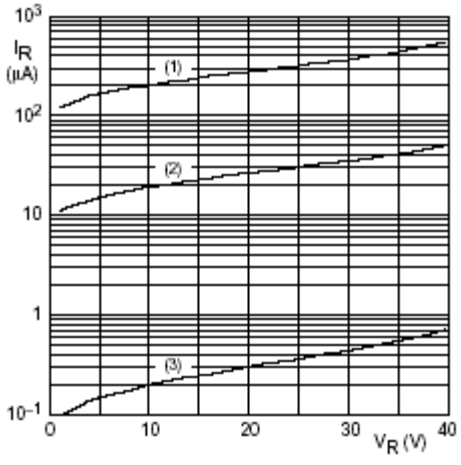
Dated : 23/11/2006



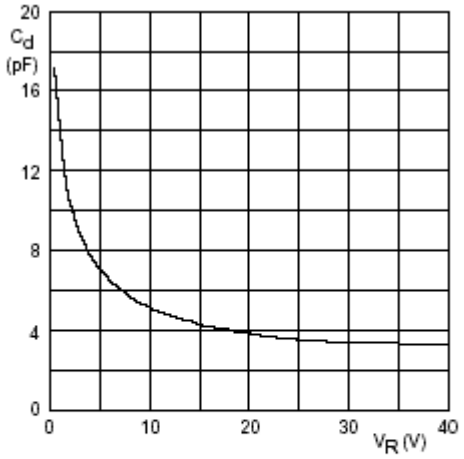
(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.

Fig.1 Forward current as a function of forward voltage; typical values.



(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.

Fig. 2 Reverse current as a function of reverse voltage; typical values.



f = 1 MHz; T_{amb} = 25 °C.

Fig. 3 Diode capacitance as a function of reverse voltage; typical values.

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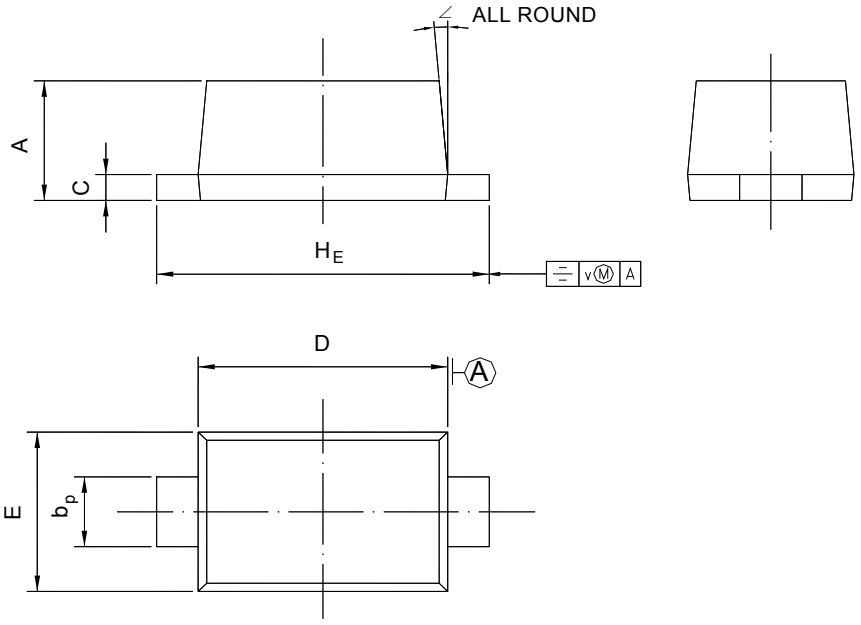
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-523**



UNIT	A	b_p	C	D	E	H_E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°